

# **isc Silicon PNP Power Transistor**

#### **DESCRIPTION**

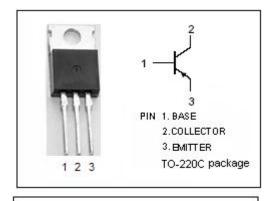
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -100V(Min)
- · High DC Current Gain-
  - :  $h_{FE}$ = 100(Min)@ ( $V_{CE}$ = -2V ,  $I_{C}$ = -1A)
- · Low Saturation Voltage-
  - :  $V_{CE(sat)} = -0.3V(Max)@ (I_C = -4A, I_B = -0.2A)$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

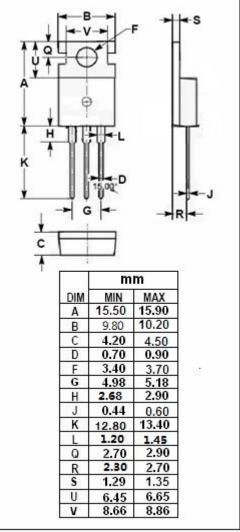


 Developed for use in switching power supplies, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for highcurrent switching.



SYMBOL	PARAMETER VALUE		UNIT
V <sub>СВО</sub>	Collector-Base Voltage	-150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-7.0	V
Ic	Collector Current-Continuous	-7.0	А
I <sub>CM</sub>	Collector Current-Peak	-14	А
I <sub>B</sub>	Base Current-Continuous	-3.5	А
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.5	10/
	Collector Power Dissipation @ T <sub>C</sub> =25°C	35	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150 °C	







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2SA1645

## **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A		-0.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	Ic= -6A; I <sub>B</sub> = -0.3A		-0.5	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A		-1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A		-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> =0		-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0		-10	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	100		
h <sub>FE-2</sub>	DC Current Gain	Ic= -1.5A; VcE= -2V	100	400	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -2V	60		

# ♦ h<sub>FE-2</sub> Classifications

M	L	K
100-200	150-300	200-400

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